# 2SB1548, 2SB1548A

### Silicon PNP epitaxial planar type

For power amplification

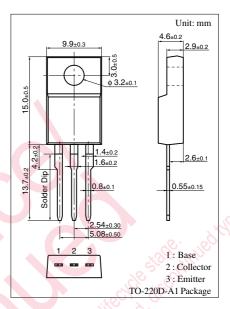
Complementary to 2SD2374 and 2SD2374A

#### ■ Features

- $\bullet$  High forward current transfer ratio  $h_{\text{FE}}$  which has satisfactory linearity
- $\bullet$  Low collector to emitter saturation voltage  $V_{\text{CE}(\text{sat})}$
- Full-pack package which can be installed to the heat sink with one screw

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter		Symbol	Rating	Unit
Collector to base	2SB1548	$V_{CBO}$	-60	V
voltage	2SB1548A		-80	
Collector to	2SB1548	$V_{CEO}$	-60	V
emitter voltage	2SB1548A		-80	
Emitter to base voltage		$V_{EBO}$	-5	V
Peak collector current		I <sub>CP</sub>	-5	A
Collector current		$I_{C}$	-3	A
Collector power	$T_C = 25^{\circ}C$	$P_{C}$	25	W
dissipation	$T_a = 25^{\circ}C$		2	
Junction temperature		T <sub>j</sub>	150	°C
Storage temperature		$T_{stg}$	-55 to +150	°C



## ■ Electrical Characteristics $T_C = 25^{\circ}C$

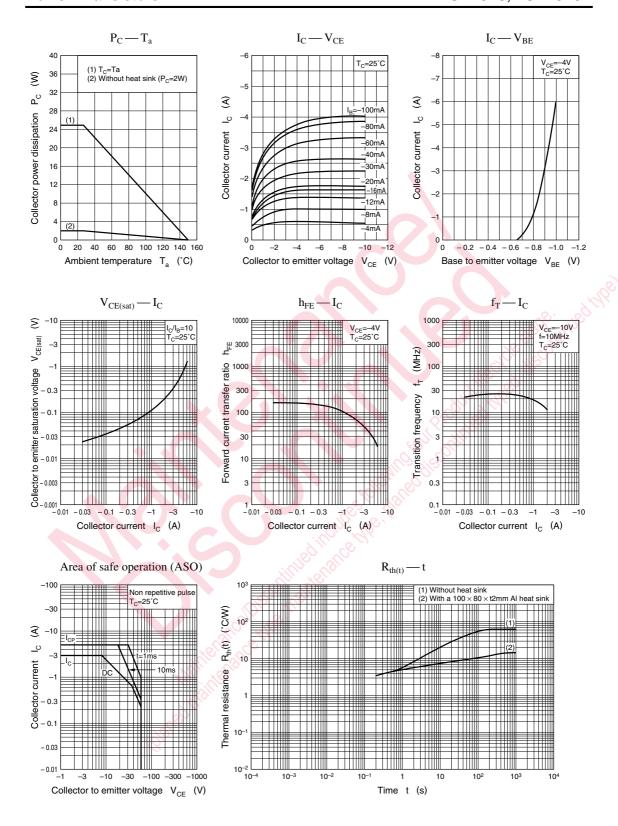
Paramete	r	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff	2SB1548	I <sub>CES</sub>	$V_{CE} = -60 \text{ V}, V_{BE} = 0$			-200	μΑ
current	2SB1548A		$V_{CE} = -80 \text{ V}, V_{BE} = 0$			-200	
Collector cutoff	2SB1548	$I_{CEO}$	$V_{CE} = -30 \text{ V}, I_{B} = 0$			-300	μΑ
current	2SB1548A		$V_{CE} = -60 \text{ V}, I_{B} = 0$			-300	
Emitter cutoff current		I <sub>EBO</sub>	$V_{EB} = -5 \text{ V}, I_{C} = 0$			-1	mA
Collector to emitter	2SB1548	$V_{CEO}$	$I_{\rm C} = -30 \text{ mA}, I_{\rm B} = 0$	-60			V
voltage	2SB1548A	4000		-80			
Forward current transfer ratio		h <sub>FE1</sub> *	$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}$	70		250	
		h <sub>FE2</sub>	$V_{CE} = -4 \text{ V}, I_{C} = -3 \text{ A}$	10			
Base to emitter voltage		$V_{BE}$	$V_{CE} = -4 \text{ V}, I_{C} = -3 \text{ A}$			-1.8	V
Collector to emitter satu	ration voltage	V <sub>CE(sat)</sub>	$I_C = -3 \text{ A}, I_B = -0.375 \text{ A}$			-1.2	V
Transition frequency	16/10	$f_T$	$V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ A}, f = 10 \text{ MHz}$		30		MHz
Turn-on time		t <sub>on</sub>	$I_C = -1 A$ , $I_{B1} = -0.1 A$ , $I_{B2} = 0.1 A$		0.5		μs
Storage time		t <sub>stg</sub>			1.2		μs
Fall time		t <sub>f</sub>			0.3		μs

Note) \*: Rank classification

Rank	Q	Р		
h <sub>FE1</sub>	70 to 150	120 to 250		

Ordering can be made by the common rank (PQ rank  $h_{FE\,I}$  = 70 to 250) in the rank classification.

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